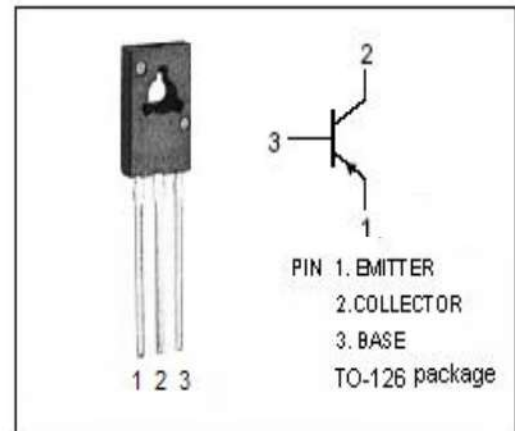


**isc Silicon PNP Power Transistor**
**BD132**
**DESCRIPTION**

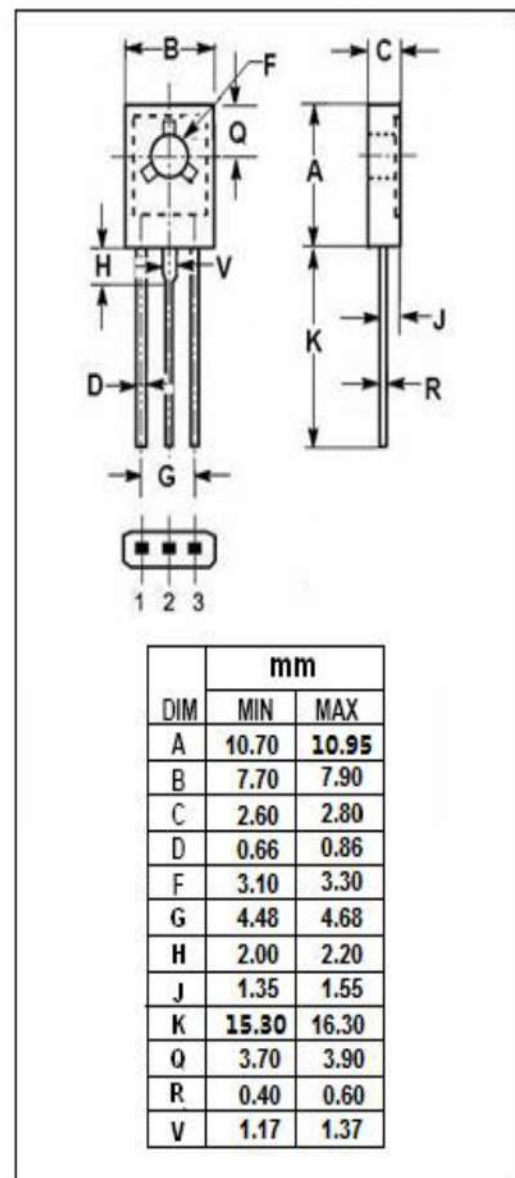
- DC Current Gain-  
:  $h_{FE} = 40(\text{Min}) @ I_C = -0.5\text{A}$
- Collector-Emitter Breakdown Voltage -  
:  $V_{(BR)CEO} = -45\text{V}(\text{Min.})$
- Complement to type BD131
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for medium power and general purpose applications.


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-70	V
$V_{CEO}$	Collector-Emitter Voltage	-45	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-3	A
$I_{CM}$	Collector Current-Peak	-6	A
$I_{BM}$	Base Current-Peak	-0.5	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	15	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$


**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	6	$^\circ\text{C/W}$

## isc Silicon PNP Power Transistor

BD132

## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -0.5\text{A}; I_B = -50\text{mA}$			-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-0.7	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C = -0.5\text{A}; I_B = -50\text{mA}$			-1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -40\text{V}; I_E = 0$ $V_{CB} = -40\text{V}; I_E = 0, T_C = 150^\circ\text{C}$			-50 -10	nA $\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -3\text{V}; I_C = 0$			-50	nA
$h_{FE-1}$	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -12\text{V}$	40			
$h_{FE-2}$	DC Current Gain	$I_C = -2\text{A}; V_{CE} = -1\text{V}$	20			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.25\text{A}; V_{CE} = -5\text{V}$	60			MHz

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